



NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI CBSL30B is Designed for

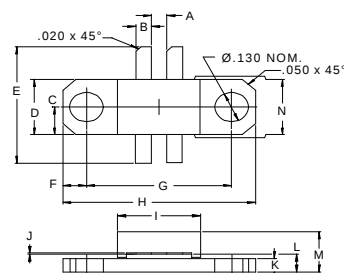
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CBO}	48 V
V_{CES}	45 V
V_{EBO}	4.0 V
P_{DISS}	43 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$3.0^\circ C/W$

PACKAGE STYLE .250 BAL FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.060 / 1.52
B	.055 / 1.40	.065 / 1.65
C		.125 / 3.18
D	.243 / 6.17	.255 / 6.48
E	.630 / 16.00	.670 / 17.01
F		.092 / 2.34
G	.555 / 14.10	.565 / 14.35
H	.739 / 18.77	.750 / 19.05
I	.315 / 8.00	.327 / 8.31
J	.002 / 0.05	.006 / 0.15
K	.055 / 1.40	.065 / 1.65
L	.075 / 1.91	.095 / 2.41
M		.190 / 4.83
N	.245 / 6.22	.257 / 6.53

ORDER CODE: ASI10583

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 50$ mA	48	50	---	V
BV_{CEO}	$I_C = 20$ mA	25	30	---	V
BV_{EBO}	$I_E = 5$ mA	3.5	4.0	---	V
I_{CBO}	$V_{CB} = 24$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	20		100	---
C_{OB}	$V_{CB} = 24$ V $f = 1.0$ MHz			25	pF
P_G	$V_{CC} = 24$ V $I_{CQ} = 2 \times 75$ mA $f = 960$ MHz $P_{OUT} = 30$ W	7.5			dB